

changed relative to the immediate prior version, except that marked up versions are not being supplied for any added claim or canceled claim.

Amended
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~~27.~~ (Amended) A gate stack, comprising:
a polysilicon layer over a semiconductive substrate;
a gate oxide layer on the polysilicon layer;
a metal silicide layer on the gate oxide layer;
a layer comprising $\text{Si}_x\text{N}_y\text{O}_z\text{:H}$ formed over and in physical contact with the metal silicide, wherein x is from 0.39 to 0.65, y is from 0.02 to 0.56, and z is from 0.05 to 0.33; the metal silicide being the product of a process in which the metal silicide is subjected to an anneal treatment after the layer comprising $\text{Si}_x\text{N}_y\text{O}_z\text{:H}$ is formed; and
a silicon nitride layer on the layer comprising $\text{Si}_x\text{N}_y\text{O}_z\text{:H}$, the polysilicon layer, the gate oxide layer, the metal silicide layer, the layer comprising $\text{Si}_x\text{N}_y\text{O}_z\text{:H}$, and the silicon nitride layer being patterned to form the gate stack.

~~32.~~ The gate stack of Claim ~~27~~, where the layer comprising $\text{Si}_x\text{N}_y\text{O}_z\text{:H}$ has a thickness of from about 250Å to about 650Å.

~~36.~~ The gate stack of claim ~~27~~ wherein y is from 0.02 to less than 0.1.

~~37.~~ The gate stack of claim ~~27~~ wherein x=0.5, y=0.37 and z=0.13.

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(New) The gate stack of claim 27 wherein the metal silicide layer comprises titanium.